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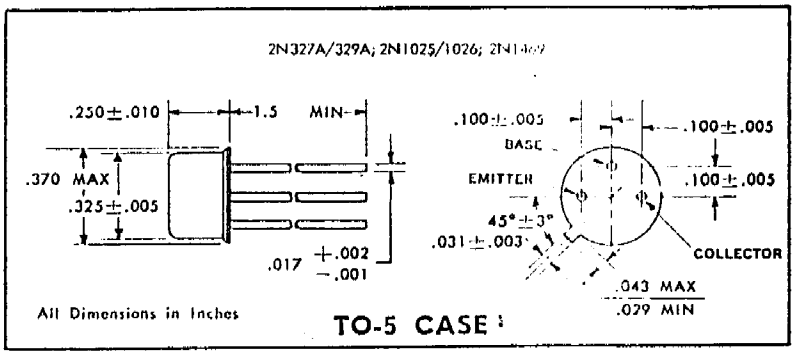
GENERAL PURPOSE
SILICON EPITAXIAL JUNCTION
PNP TRANSISTORS

2N935 — 2N327A
2N936 — 2N328A
2N937 — 2N329A
2N938 — 2N1025
2N939 — 2N1026
2N940 — 2N1469

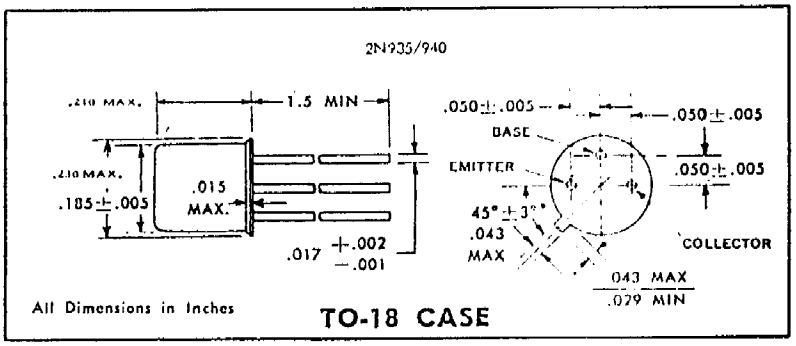
ELECTRICAL DATA ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	2N935 2N327A	2N936 2N328A	2N937 2N329A	UNITS
Collector to Emitter Voltage	BV_{CEO}	-40	-35	-30	V
Collector to Base Voltage	BV_{CBO}	-50	-50	-50	V
Emitter to Base Voltage	BV_{EBO}	-20	-20	-20	V
Collector Current	I_C	-100mA			
Power Dissipation (free air)	P_D	250mW			
Junction Temp. (Oper. & Store)	T_J	-65°C to +165°C			
Lead Temp. (1/16" ±1/32" From Case)	T_L	240°C for 10 sec.			
Derating Factor (free air)	D_F	1.85mW/°C			

PARAMETER	SYMBOL	2N938 2N1025	2N939 2N1026	2N940 2N1469	UNITS
Collector to Emitter Voltage	BV_{CEO}	-35	-35	-35	V
Collector to Base Voltage	BV_{CBO}	-40	-40	-40	V
Emitter to Base Voltage	BV_{EBO}	-40	-40	-40	V
Collector Current	I_C	-100mA			
Power Dissipation (free air)	P_D	250mW			
Junction Temp. (Oper. & Store)	T_J	-65°C to +165°C			
Lead Temp. (1/16" ±1/32" From Case)	T_L	230°C for 10 sec.			
Derating Factor (free air)	D_F	1.66mW/°C			



TO-5 CASE



TO-18 CASE

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL CHARACTERISTICS: T_A = 25°C (UNLESS OTHERWISE STATED)

PARAMETER	SYMBOL	CONDITION	2N935/2N327A			2N936/2N328A			2N937/2N329A			UNITS
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Collector-Base Leakage Current	I_{CBO}	V_{CB} = -30V	-	5.0	100	-	5.0	100	-	5.0	100	nA
Emitter-Base Leakage Current	I_{EBO}	V_{EB} = -20V	-	5.0	100	-	5.0	100	-	5.0	100	nA
Collector Saturation Voltage	$V_{CE(sat)}$	I_C = -5mA, I_B = -2mA	-	-	0.3	-	-	0.5	-	-	0.6	V
A.C. Current Gain	h_{fe}	V_{CE} = -6V, I_E = 1.0mA, f = 1KC	9	14	22	18	28	44	36	60	88	
Collector to Base Capacitance	C_{ob}	V_{CB} = -5V, f = 100KC	-	70	110	-	70	110	-	70	110	pfd
Alpha Cutoff Frequency	f_{ab}	V_{CB} = -6V, I_E = 1.0mA	0.15	0.2	-	0.2	0.3	-	0.25	0.5	-	MC
Spot Noise Figure	N.F.	I_C = -1.0mA, Rg = 1KΩ	-	18	-	-	18	-	-	18	-	db

PARAMETER	SYMBOL	CONDITION	2N938/2N1025			2N939/2N1026			2N940/2N1469			UNITS
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Collector-Base Leakage Current	I_{CBO}	V_{CB} = -35V	-	1.0	25	-	1.0	25	-	1.0	25	nA
Emitter-Base Leakage Current	I_{EBO}	V_{EB} = -35V	-	1.0	25	-	1.0	25	-	1.0	25	nA
Collector Saturation Voltage	$V_{CE(sat)}$	I_C = -5mA, I_B = -2mA	-	-	0.3	-	-	0.3	-	-	0.3	V
A.C. Current Gain	h_{fe}	V_{CE} = -6V, I_E = 1.0mA, f = 1KC	9	15	22	18	30	44	36	60	88	
Collector to Base Capacitance	C_{ob}	V_{CB} = -6V, f = 1MC	-	7	12	-	7	12	-	7	12	pfd
Alpha Cutoff Frequency	f_{ab}	V_{CB} = -6V, I_E = 1.0mA	1.0	-	-	2.0	-	-	2.0	-	-	MC
Spot Noise Figure	N.F.	I_C = -1.0mA, Rg = 1KΩ	-	-	25	-	-	25	-	-	25	db